

	Type	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r s
1	BRS	68	etch\$3 same ("dual damascene") same ("metal line")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:39		0
2	BRS	37	(organic same dielectric same "low k") same "dual damascene"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:40		0
3	BRS	80	(organic same dielectric same "low k") and "dual damascene"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:09		0
4	BRS	19	(organic same dielectric same "low k") and "dual damascene" and (metal adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:09		0
5	BRS	62	(organic same dielectric same "low k") same (photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 18:50		0
6	BRS	7	((inorganic same dielectric same "low k") and "dual damascene") and (metal adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:10		0
7	BRS	36	(inorganic same dielectric same "low k") and "dual damascene"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/13 19:16		0
8	BRS	316	etch\$3 and ("dual damascene") and ("metal line")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 15:34		0
9	BRS	87	etch\$3 same ("dual damascene") same ("metal line")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 15:34		0
10	BRS	53	(etch\$3 and ("dual damascene") and ("metal line")) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:20		0

	Type	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r s	E r r o r s
11	IS&R	0	("etch\$3 same ("dual damascene")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 15:42			0
12	IS&R	0	("etch\$3 same "dual damascene").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 15:03			0
13	BRS	1392	etch\$3 same ("dual damascene")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 15:03			0
14	BRS	842	(etch\$3 same ("dual damascene")) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 16:02			0
15	IS&R	0	("etch\$3 same ("dual damascene") same ((gate and source and drain) or transistor or FET)).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 15:43			0
16	BRS	29	etch\$3 same ("dual damascene") same ((gate and source and drain) or transistor or FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 16:01			0
17	BRS	355	(etch\$3 same ("dual damascene")) and ((gate and source and drain) or transistor or FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 16:02			0
18	BRS	267	((etch\$3 same ("dual damascene")) and ((gate and source and drain) or transistor or FET)) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 16:02			0
19	BRS	22	((etch\$3 same ("dual damascene")) and ((gate and source and drain) or transistor or FET)) and 438/\$.ccls.) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 17:27			0
20	BRS	142	(SiO2 or quartz or "silicon dioxide") same ("low k" or "low dielectric") same (CORAL or "black diamond" or FSG or XLK or Z3MS or HSQ or "hydrogen silsequioxane")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 17:56			0

	Type	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
21	BRS	12	((SiO2 or quartz or "silicon dioxide") same ("low k" or "low dielectric") same (CORAL or "black diamond" or FSG or XLK or Z3MS or HSQ or "hydrogen silsesquioxane")) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:03			0
22	BRS	16	Z3MS or XLK	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:02			0
23	BRS	2028	Z3MS or XLK or BCB OR MSQ OR HSQ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:03			0
24	BRS	2039	Z3MS or XLK or BCB OR MSQ OR HSQ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:03			0
25	BRS	735	(Z3MS or XLK or BCB OR MSQ OR HSQ) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:05			0
26	BRS	2027	BCB OR MSQ OR HSQ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:04			0
27	BRS	958	(BCB OR MSQ OR HSQ) SAME DIELECTRIC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:04			0
28	BRS	230	((BCB OR MSQ OR HSQ) SAME DIELECTRIC) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:04			0
29	BRS	621	(BCB OR MSQ) SAME DIELECTRIC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:07			0
30	BRS	140	((BCB OR MSQ) SAME DIELECTRIC) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:05			0

	Type	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r s
31	BRS	17	(HOSP) SAME DIELECTRIC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 18:08		0
32	BRS	2	((organic same dielectric same "low k") same "dual damascene") and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/07 11:18		0
33	BRS	50	(organic same dielectric same "low k") same "dual damascene"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/07 10:04		0
34	BRS	44	(etch\$3) same mask same (dielectric or insulat\$3) same (self adj align\$4) same "dual damascene"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/07 10:46		0
35	BRS	47	(mask) same ("low k" or "low dielectric") same (CORAL OR "black diamond" or FSG or XLK or Z3MS or HSQ or "hydrogen silsesquioxane" or FLARE OR SILK OR "BLACK DIAMOND") SAME ETCH\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/07 11:16		0
36	BRS	58	(mask) same ("low k" or "low dielectric") same (CORAL OR "black diamond" or polyimide or HOSP or BCB or MSQ or FLARE OR SILK) SAME ETCH\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/07 11:18		0
37	BRS	15	((mask) same ("low k" or "low dielectric") same (CORAL OR "black diamond" or polyimide or HOSP or BCB or MSQ or FLARE OR SILK) SAME ETCH\$3) and @pd<=20000430	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/07 11:18		0